

**Production Of Silicon By Reacting Silicon Oxide And Silicon Carbide,
Optionally In The Presence Of A Second Carbon Source**

Abstract

The invention relates to a method for producing silicon by reacting silicon oxide at an elevated temperature, silicon carbide and, optionally, a second carbon source being added to the reaction mixture. The invention further relates to a composition that can be used in the disclosed method. The essential part of the invention is the use of silicon carbide as a reaction initiator and/or reaction accelerator during the production of silicon or, alternatively, in nearly equimolar amounts for the production of silicon.

No Fig.